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Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/535,015
		Filing Date	March 24, 2000
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2811
		Examiner Name	Sara W. Crane
Sheet 1 of 2	Attorney Docket Number	0756-2131	

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FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³ Number ⁴ Kind Code ⁵ (if known)				
		EP 0 178 447	—	04/23/1986	—	Eng.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SC		STOEMENOS et al., <i>Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold</i> , Appl. Phys. Lett., Volume 58, No. 11, March 18, 1991, Pages 1196-1198.	
		KUZNETSOV et al., <i>Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting from Ion Implantation and Annealing</i> , Nuclear Instruments and Methods in Physics Research, 880/881, 1993, Pages 990-993.	
		HATALIS et al., <i>High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films</i> , IEEE Electron Device Letters, Vol. EDL 8, No. 8, August 1987, Pages 361-364.	
		LAU et al., <i>Solid Phase Epitaxy Silicide-Forming Systems</i> , Thin Solid Films, Volume 47, No. 3, 1977, Pages 313-322.	
		KAWAZU et al., <i>Initial Stage of the Interfacial Reaction Between Nickel and Hydrogenated Amorphous Silicon</i> , Japanese Journal of Applied Physics, Volume, 29, No. 4, April 1, 1990, Pages 729-738.	
		HEMPEL et al., <i>Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films</i> , Solid State Communications, Volume 85, No. 11, 1993, Pages 921-924.	
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SC		DVURECHENSKII et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol. (a), Volume 95, No. 635, 1986, Pages 635-640.	

no date listed

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Examiner Signature	/Sara Crane/	Date Considered	08/30/2006
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SC		HAYZELDEN et al., <i>Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films</i> , J. Appl. Phys., Volume 73, No. 12, June 15, 1993, Pages 8279-8289.	
		KUZNETSOV et al., <i>Silicide Precipitate Formation and Solid Phase Re-Growth of Ni⁺-Implanted Amorphous Silicon</i> , Inst. Phys. Conf. Ser. No. 134.4: Proceedings of the Royal Microscopical Society Conf., April 5-8, 1993, Pages 191-194.	
		BAKER, JR. et al., <i>Field Effect Transistor</i> , IBM Technical Disclosure Bulletin, Volume 11, No. 7, December 1968, Page 849.	
		WOLF, <i>Silicon Processing for the VLSI Era</i> , Volume 2: Process Integration, 1990, Pages 273-274.	
SC		CAUNE et al., <i>Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals</i> , Applied Surface Science, Volume 36, January 1, 1989, Pages 597-604.	

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